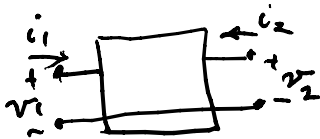
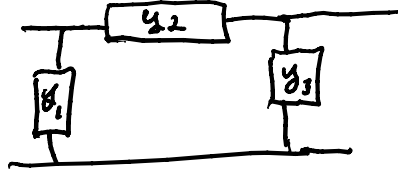


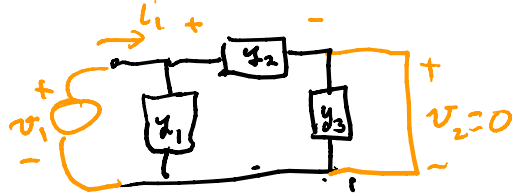
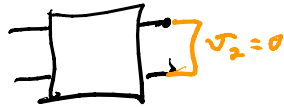
P.487 = BJT small signal "hybrid" pi  
 Y matrix = appendix B (admittance)  
 $\pi$  equivalent circuit

EE 303 H  
 09/22/09



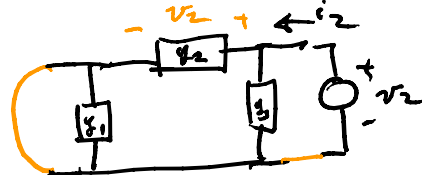
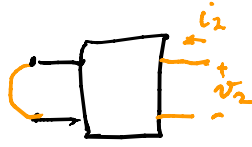
$$\begin{bmatrix} i_1 \\ i_2 \end{bmatrix} = \begin{bmatrix} y_{11} & y_{12} \\ y_{21} & y_{22} \end{bmatrix} \begin{bmatrix} v_1 \\ v_2 \end{bmatrix}$$

$$y_{11} = \left. \frac{i_1}{v_1} \right|_{v_2=0}$$



$$y_{11} = y_{11} - y_2 = y_1 + y_2$$

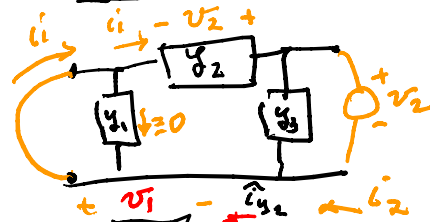
$$y_{22} = \left. \frac{i_2}{v_2} \right|_{v_1=0}$$



$$y_{22} = y_3 + y_2$$

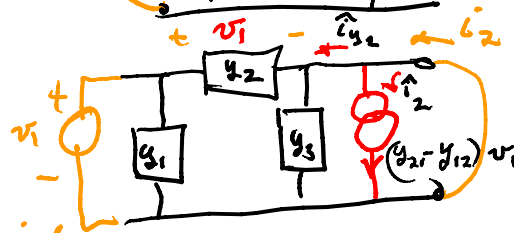
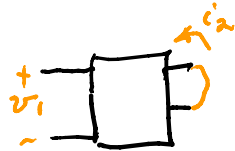
$$y_{12} = -y_{21}$$

$$y_{12} = \left. \frac{i_1}{v_2} \right|_{v_1=0}$$



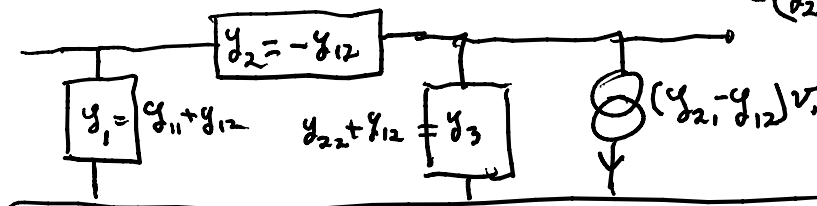
$$y_{12} = -y_2$$

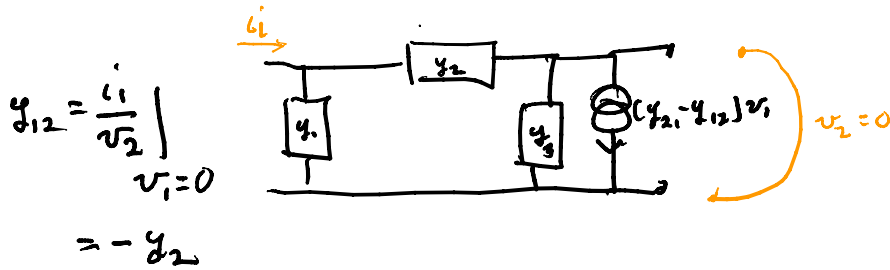
$$y_{21} = \left. \frac{i_2}{v_1} \right|_{v_2=0}$$



$= -y_2 \Rightarrow y_{21} = y_{12}$  if reciprocal  
 but  $y_{21} \neq y_{12}$  in general  
 (for transistor)

$$i_2 = \hat{i}_{y_2} + \hat{i}_2 = -y_2 v_1 + \hat{i}_2 = y_{21} v_1 \Rightarrow \hat{i}_2 = y_{21} v_1 + y_2 v_1 = (y_{21} - y_2) v_1$$

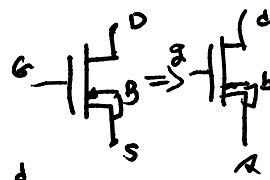




$y_{11} = \left. \frac{i_1}{v_1} \right|_{v_2=0} = y_2 \frac{v_1}{v_1} + y_1 \frac{v_1}{v_1} = y_1 + y_2$

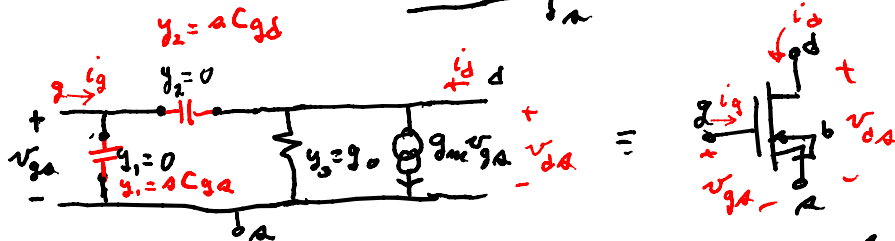
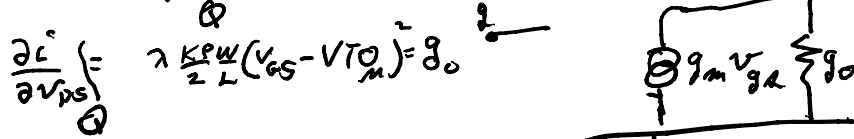
$y_{22} = \left. \frac{i_2}{v_2} \right|_{v_1=0} = y_2 + y_3$

has no current in the dependent source



$\pi$  equivalent for the MOS  
 if in saturation  
 NMOS  $i_D = \frac{K_P W}{2L} (V_{GS} - V_{TO_M})^2 (1 + \lambda V_{DS})$

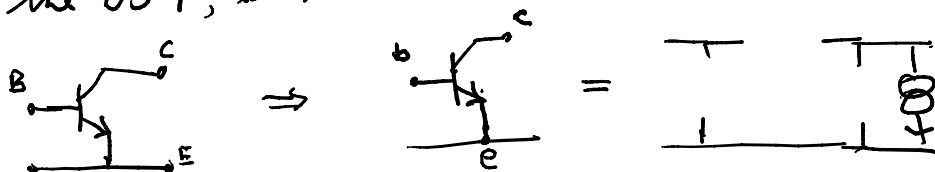
$\frac{\partial i_D}{\partial V_{GS}} = \frac{2K_P W}{2L} (V_{GS} - V_{TO_M})(1 + \lambda V_{DS}) = \underline{g_m}$



is the  $\pi$ -equivalent for the MOS transistor  
 (small signal, linearized)

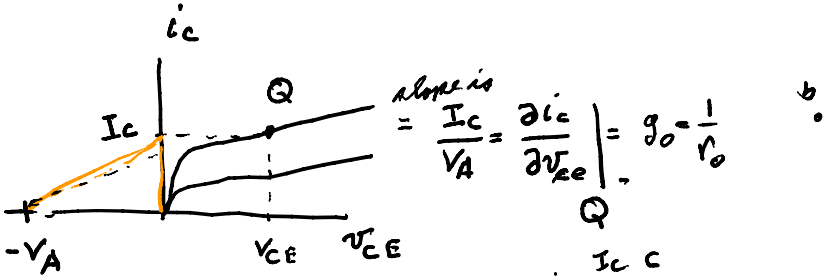
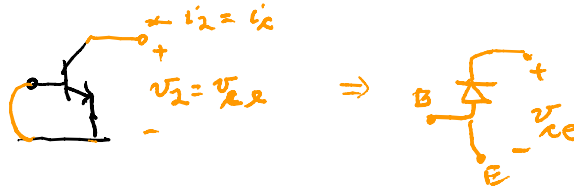
$$Y(a) = \begin{bmatrix} ACga + ACgd & -ACgd \\ -ACgd + g_m & go + ACgd \end{bmatrix}$$

Do for the BJT, see p. 487

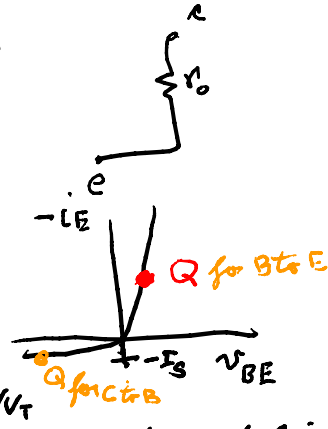
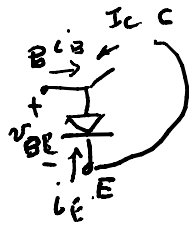


$i_c = \beta i_b$ , when bias we usually forward bias the B to E diode & back bias the B to C diode

$$y_{22} = \left. \frac{i_2}{v_2} \right|_{v_1=0} = \left. \frac{i_c}{v_{ce}} \right|_{v_1=0}$$



$$y_{11} = \left. \frac{i_1}{v_1} \right|_{v_2=0} = \left. \frac{i_b}{v_{be}} \right|_Q$$



$$\frac{\partial(-I_E)}{\partial v_{BE}} = \text{slope of diode curve at } Q$$

$$i_D \approx I_S e^{v_D/v_T}$$

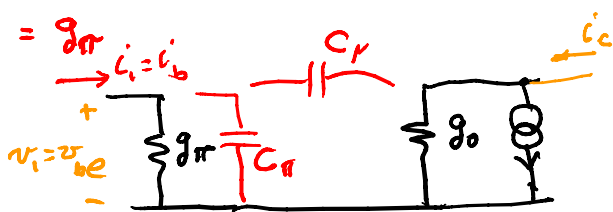
$$\frac{\partial(-I_E)}{\partial v_{BE}} = \frac{\partial i_D}{\partial v_D} = \frac{I_S}{v_T} e^{v_D/v_T} = \frac{-I_E}{v_T}$$

(as forward bias can ignore  $-I_S$  as it is very small)

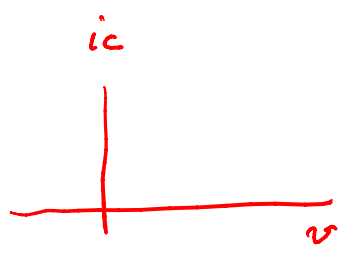
need  $\frac{\partial i_b}{\partial v_{BE}}$  for  $y_{11}$

$$i_c = \beta i_b = -\alpha I_E \Rightarrow i_b = -\frac{\alpha}{\beta} I_E$$

$$y_{11} = \frac{\partial i_b}{\partial v_{BE}} = \frac{-I_E}{v_T} \cdot \frac{\alpha}{\beta} = \frac{I_c}{v_T} \cdot \frac{1}{\beta}$$



$\Rightarrow$   $\pi$  equivalent for a BJT



$$y_{21} = \left. \frac{\partial i_2}{\partial v_1} \right|_Q = \left. \frac{i_c}{v_{BE}} \right|_Q = \frac{i_c}{i_b} \cdot \frac{i_b}{v_{be}} = \beta \cdot g_{\pi}$$

$$(y_{21} - y_{22})v_1 = \beta g_{\pi} \cdot v_{be} = \frac{I_c}{v_T} \cdot v_{be}$$

$$= g_m v_{be}$$

$$g_m = I_c / v_T$$

$$g_{\pi} = \frac{I_c}{v_T} \cdot \frac{1}{\beta} = \frac{g_m}{\beta}$$